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Docket Number (Optional)

SETI-0001

Application Number

09/966563

Applicant(s)

Khan et al.

Filing Date

September 27, 2001

Group Art Unit

2814

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>		Docket Number (Optional) SETI-0001	Application Number 09/966563
		Applicant(s) Khan et al.	
		Filing Date September 27, 2001	Group Art Unit 2814

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Notice of References Cited	Application/Control No. 09/966,563	Applicant(s)/Patent Under Reexamination KHAN ET AL.	
	Examiner Long Pham	Art Unit 2814	Page 1 of 1

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